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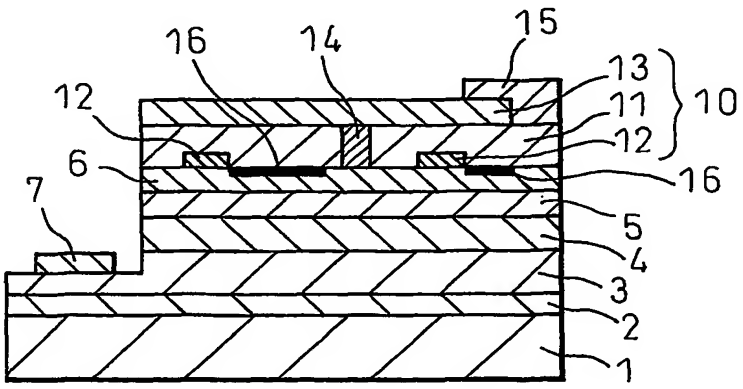
(54) Title: GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR LIGHT-EMITTING DEVICE AND ELECTRODE FOR THE SAME




(57) Abstract: An object of the present invention is to provide a light-permeable electrode for use in a gallium nitride-based compound semiconductor light-emitting device, the electrode having improved light permeability and contact resistance. The inventive electrode comprises a light-permeable first layer which is in contact with a surface of a p-contact layer in a gallium nitride-based compound semiconductor light-emitting device and which is capable of providing ohmic contact, and a second layer which is in contact with a part of a surface of said p-contact layer, wherein the first layer comprises a metal, or an alloy of two or more metals, selected from a first group consisting of Au, Pt, Pd, Ni, Co, and Rh, and the second layer comprises an oxide of at least one metal selected from a second group consisting of Ni, Ti, Sn, Cr, Co, Zn, Cu, Mg, and In.

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